

General Description:

The LWS6T7AM uses SGT technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is SOT23, which accords with the ROHS standard and Halogen Free standard.

Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances

Applications:

- DC-DC Converter
- Portable Equipment
- Power Management

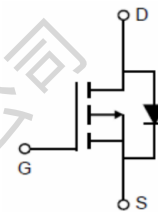


V_{DSS}	-60	V
I_D	-2.5	A
P_D	1.5	W
$R_{DS(ON)}$ TYPE	90	m Ω

Marking and Pin Assignment



Inner Equivalent Principium Chart



Package Marking and Ordering Information:

Marking	Part Number	Package	Packing	Qty.
S6T7A	LWS6T7AM	SOT23	Reel	3000 Pcs

Absolute Maximum Ratings:

Symbol	Parameter	Value	Units
V_{DSS}	Drain-to-Source Voltage	-60	V
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$	-2.5
	Continuous Drain Current	$T_C=100^\circ\text{C}$	-1.6
I_{DM}^{al}	Pulsed Drain Current	-10	A
V_{GS}	Gate-to-Source Voltage	± 20	V
P_D	Power Dissipation	1.5	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	150, -55 to 150	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	260	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Value	Units
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	80	$^\circ\text{C}/\text{W}$

Electrical Characteristic ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified):

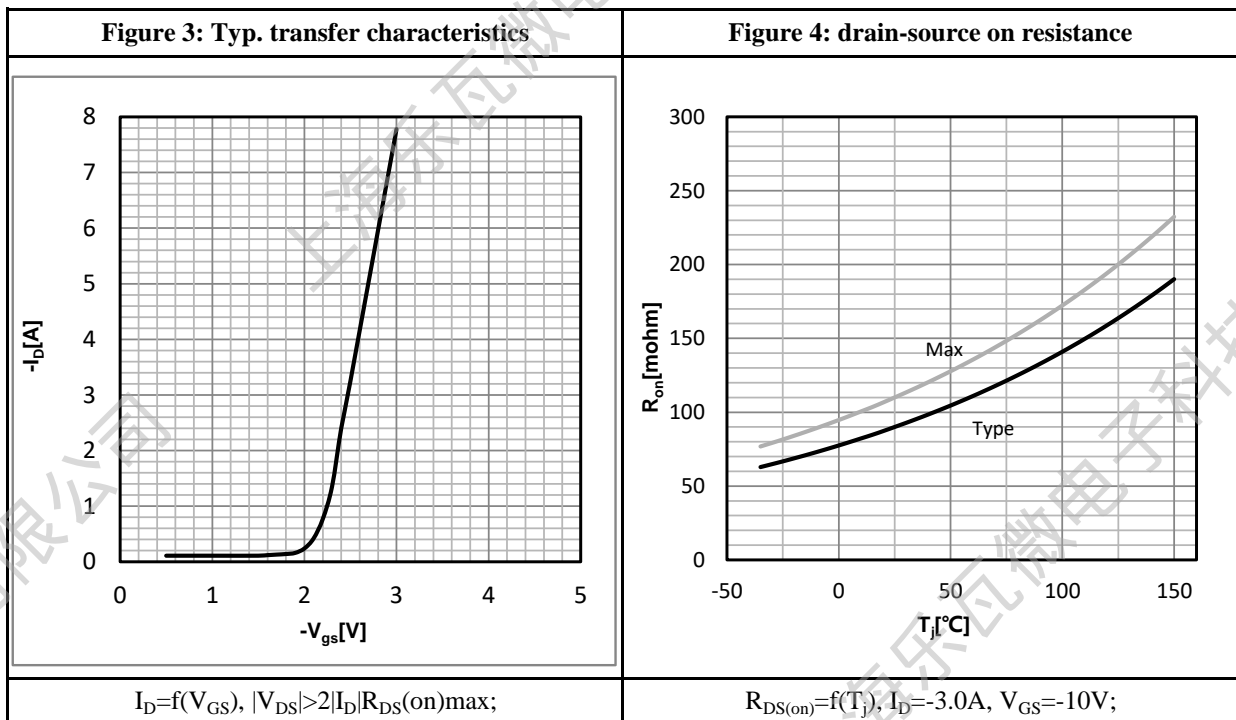
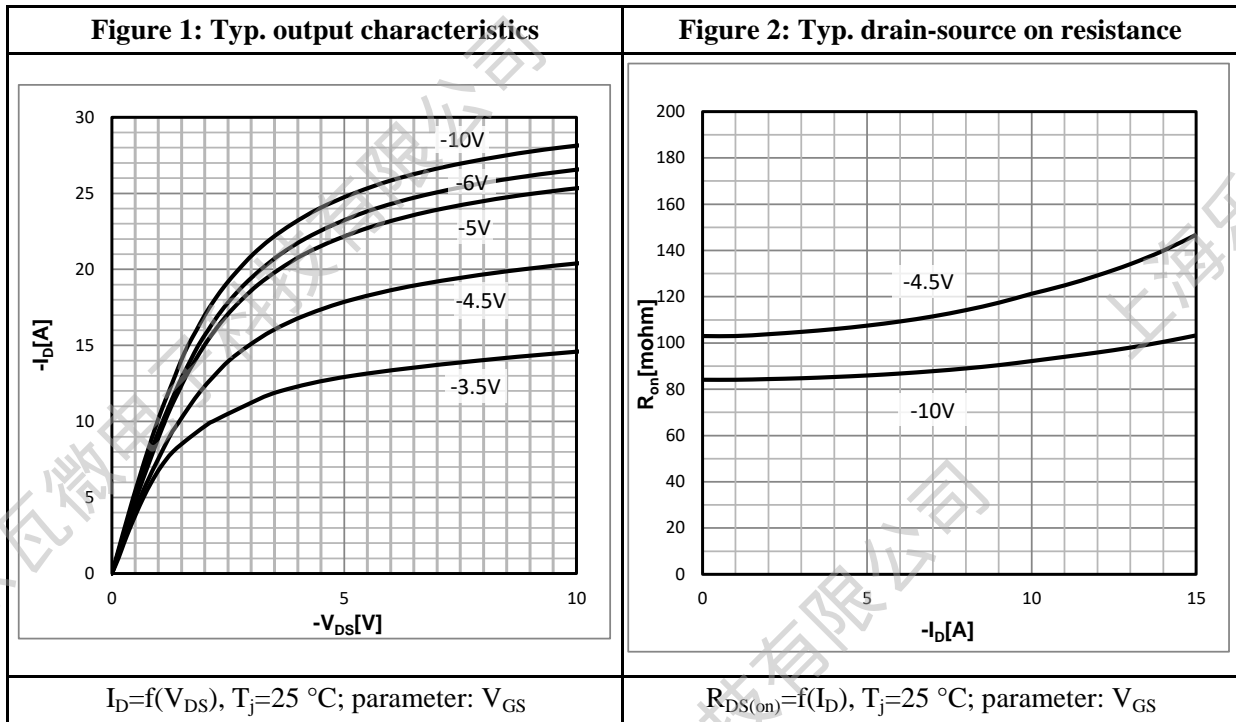
Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-60	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=-60V, V_{GS}=0V$	--	--	1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=-20V, V_{DS}=0V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=+20V, V_{DS}=0V$	--	--	-100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.2	-1.6	-2.0	V
$R_{DS(ON)1}$	Drain-to-Source On-Resistance	$V_{GS}=-10V, I_D=-3.0A$	--	90	110	$m\Omega$
$R_{DS(ON)2}$	Drain-to-Source On-Resistance	$V_{GS}=-4.5V, I_D=-2.0A$	--	110	150	$m\Omega$

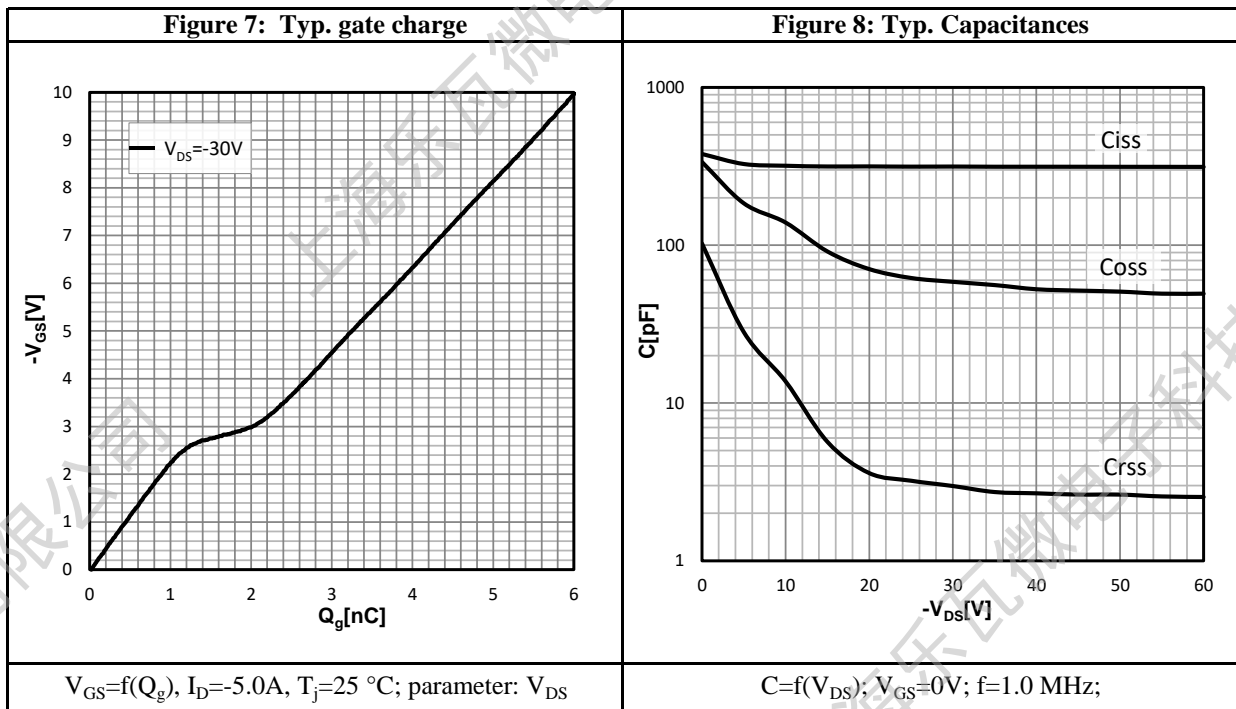
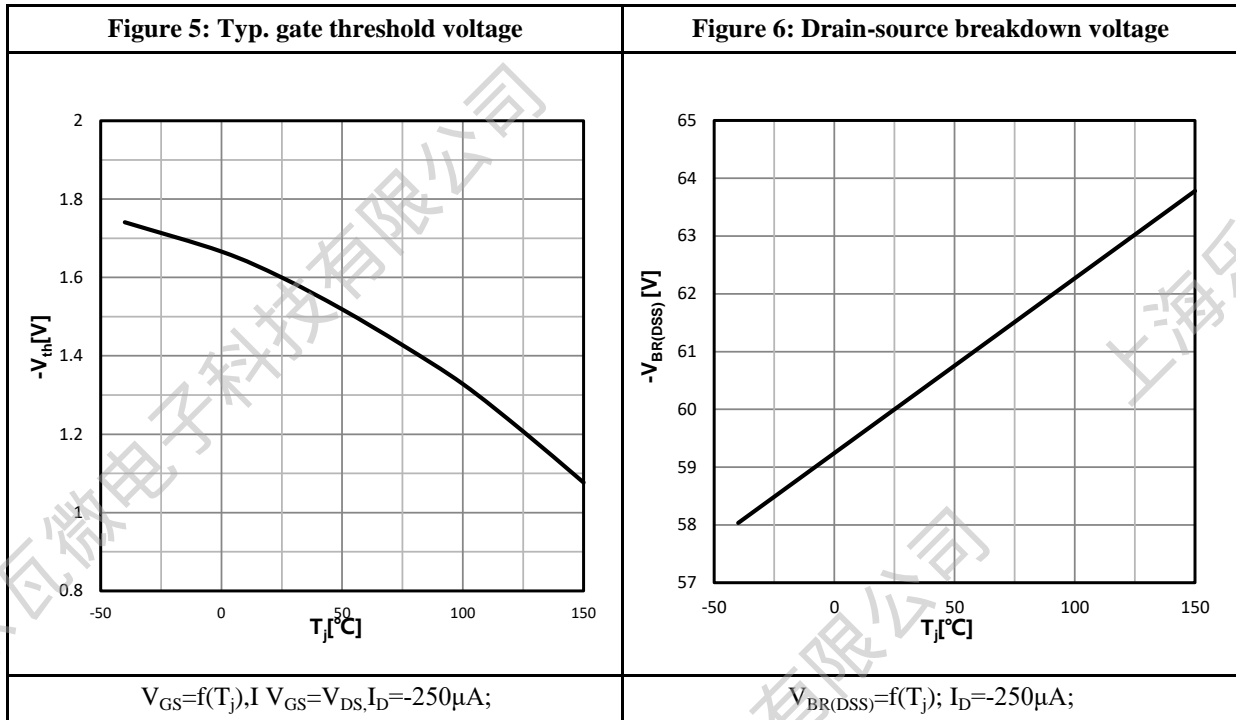
Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS} = 0V$	--	315	--	pF
C_{oss}	Output Capacitance	$V_{DS} = -30V$	--	58.6	--	
C_{rss}	Reverse Transfer Capacitance	$f = 1.0MHz$	--	2.98	--	

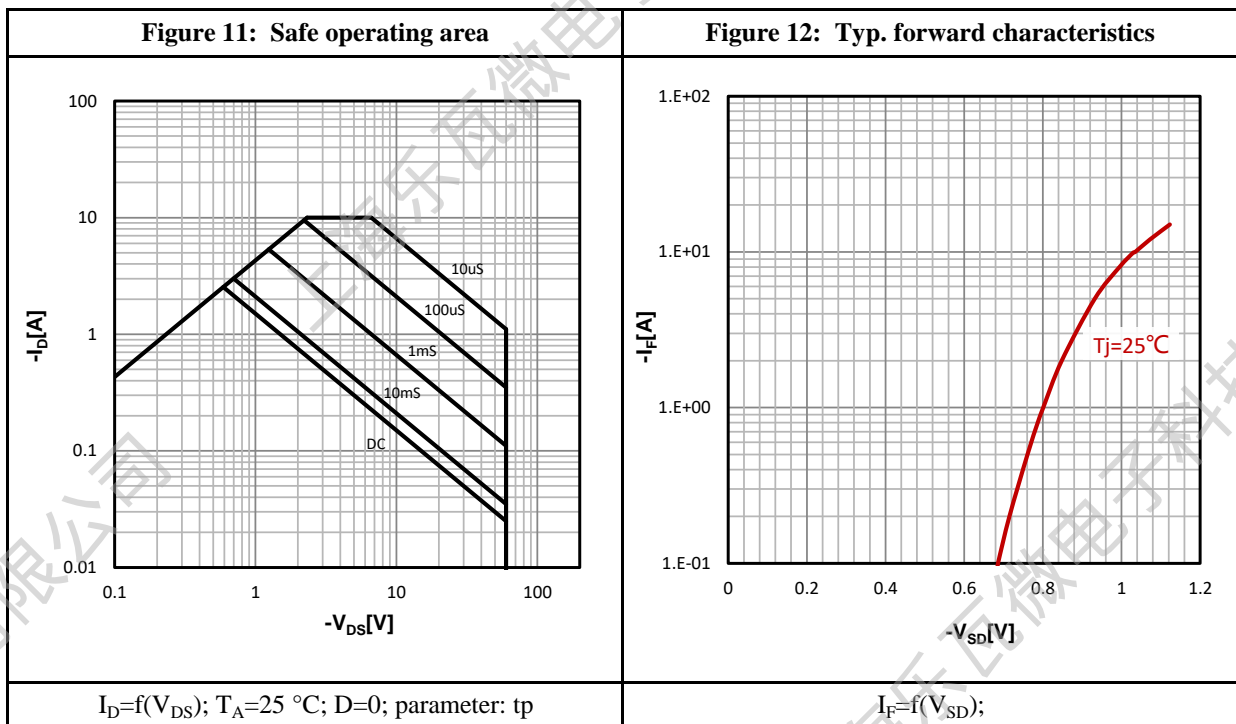
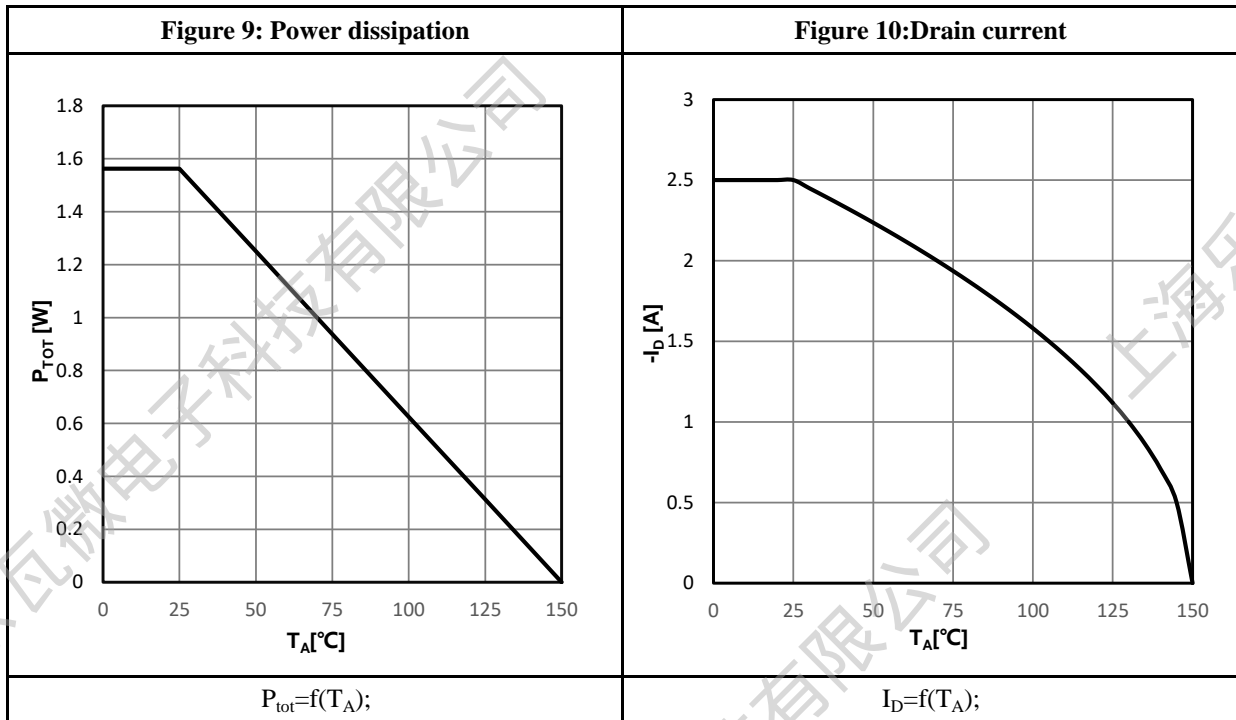
Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D = -2.0A$	--	6.8	--	ns
t_r	Rise Time	$V_{DS} = -30V$	--	8	--	
$t_{d(OFF)}$	Turn-Off Delay Time	$V_{GS} = -10V$	--	16	--	
t_f	Fall Time	$R_G = 5.0\Omega$	--	4	--	
Q_g	Total Gate Charge	$V_{GS} = -10V$	--	6.03	--	nC
Q_{gs}	Gate Source Charge	$V_{DS} = -50V$	--	0.97	--	
Q_{gd}	Gate Drain Charge	$I_D = -5.0A$	--	0.72	--	

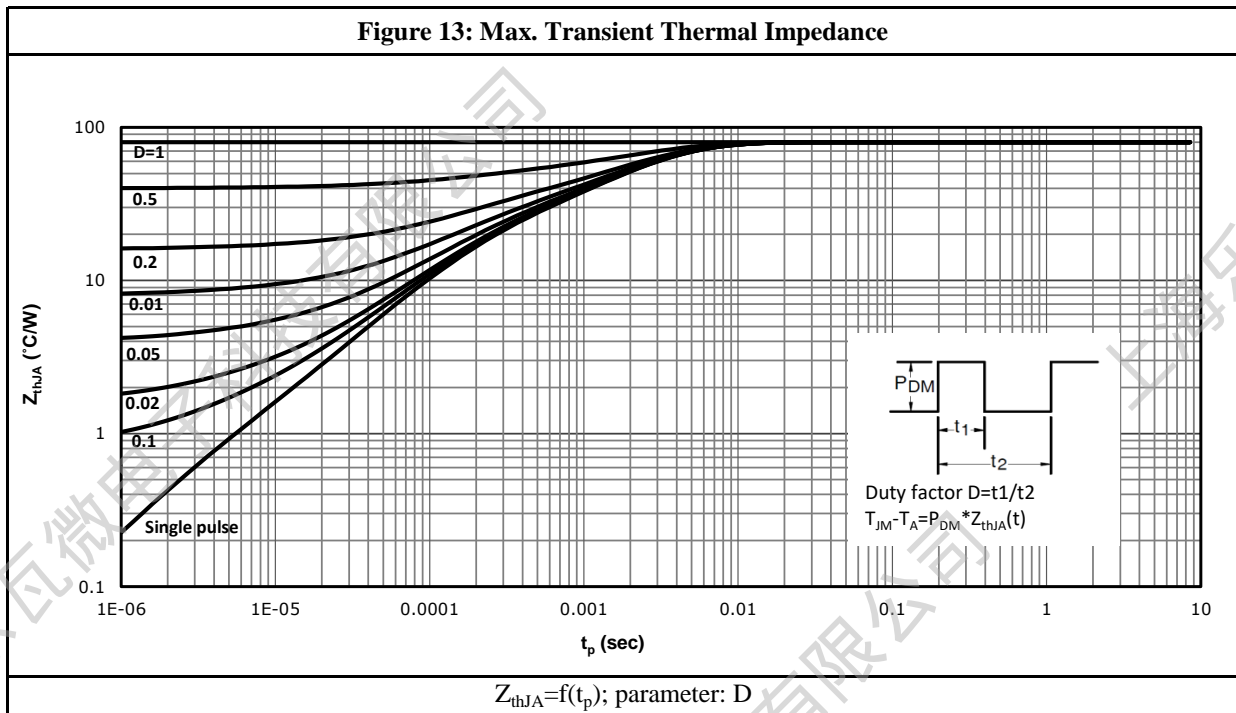
Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	$T_C = 25\text{ }^\circ\text{C}$	--	--	-2.5	A
V_{SD}	Diode Forward Voltage	$I_S = -2.0A, V_{GS} = 0V$	--	--	-1.2	V

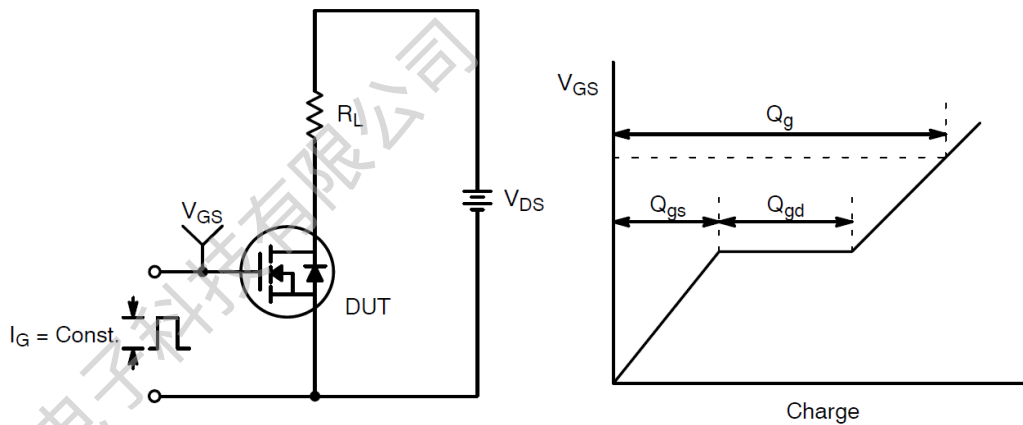
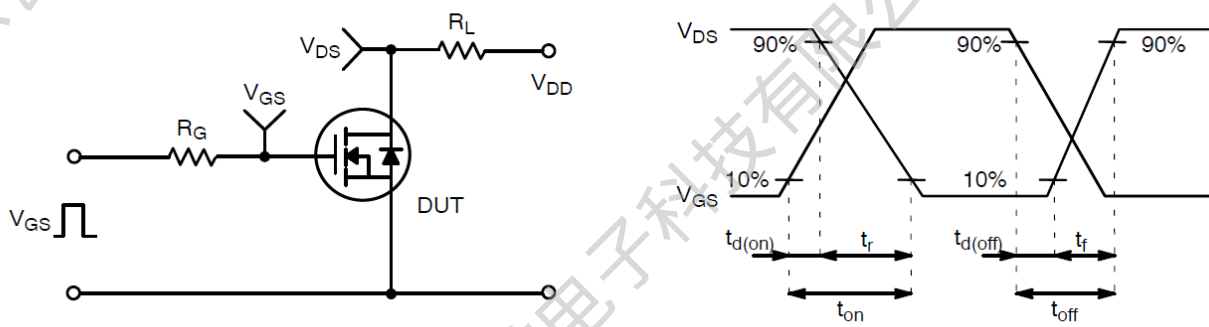
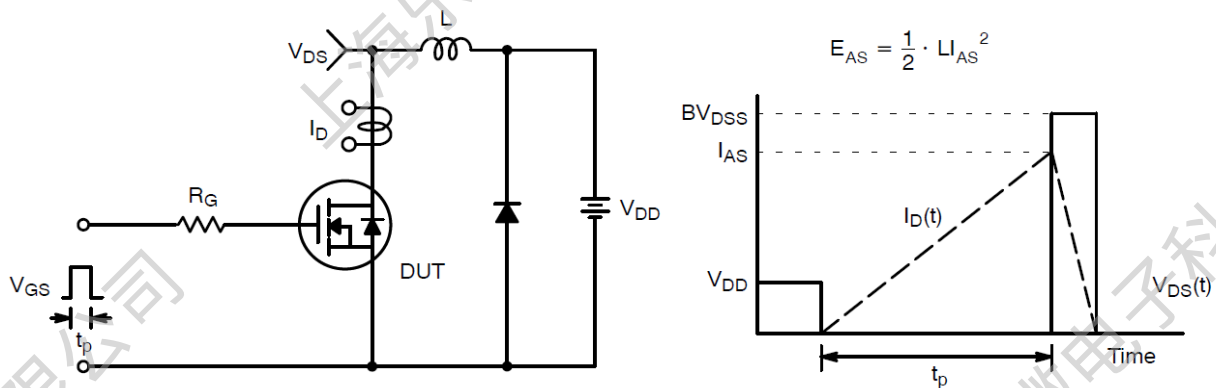
a1: Repetitive rating; pulse width limited by maximum junction temperature

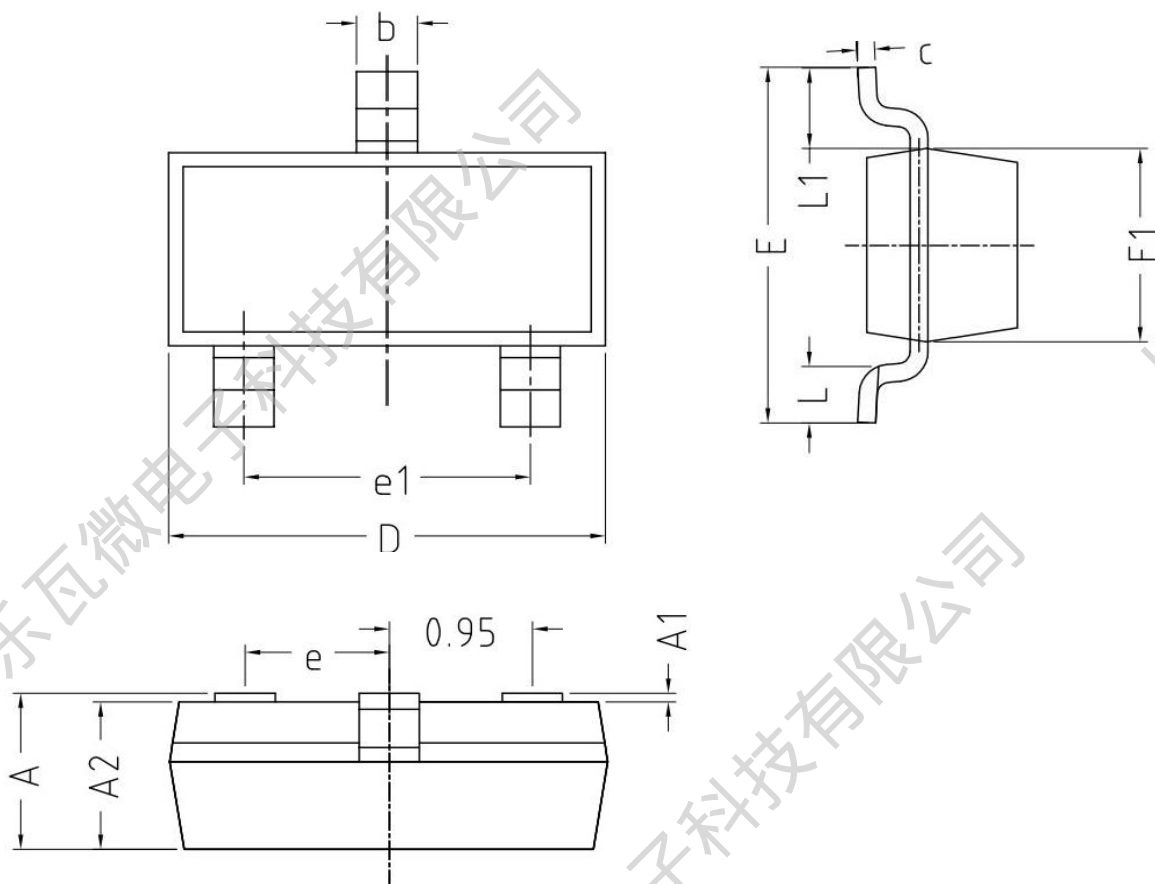
Characteristics Curve:








Test Circuit & Waveform:

Figure 14: Gate Charge Test Circuit & Waveform

Figure 15: Resistive Switching Test Circuit & Waveforms

Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

Package Outline:

COMMON IN DIMENSION (MM)

Symbol	Min.	Nom.	Max.
A	0.900	1.050	1.150
A1	0.000	0.050	0.100
A2	0.900	1.000	1.050
b	0.300	0.400	0.500
C	0.100	0.130	0.200
D	2.800	2.900	3.000
E	2.250	2.400	2.550
E1	1.200	1.300	1.400
e	0.950 TYP		
e1	1.800	1.900	2.000
L	0.290	0.390	0.490
L1	0.550REF		

Revision History:

Revison	Date	Descriptions
Rev 1.0	Apr.2023	Initial Version

Disclaimer:

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Mailing Address: Room 301, Building 2, No.1690 CaiLun Road, China (Shanghai) Pilot Free Trade Zone
Shanghai Lewa Micro-electronics Technology Co., Ltd

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